SILICON GENESIS CORPORATION ISSUED PATENTS

Title - Description	Country	Patent No.
Method and Structure for Fabricating Bonded Substrate Structures Using Thermal Processing to Remove Oxygen Species	USA	7598153
Method and System for Fabricating Strained Layers for the Manufacture of Integrated Circuits	USA	7595499
Method and Structure for Implanting Bonded Substrates for Electrical Conductivity	USA	7547609
Method and Apparatus for Flag-Less Wafer Bonding Tool	USA	7479441
Method and Device for Controlled Cleaving Process	USA	7470600
Method for Fabricating Semiconductor Devices Using Strained Silicon Bearing Material	USA	7462526
Manufacturing Strained Silicon Substrates Using a Backing Material	USA	7427554
Controlled Process and Resulting Device	USA	7410887
A Method and Structure for Implanting Bonded Substrates for Electrical Conductivity	USA	7399680
Method and System for Fabricating Strained Layers for the Manufacture of Integrated Circuits	USA	7391047
Method and System for Lattice Space Engineering	USA	7390724
Cleaving Process to Fabricate Multilayered Substrates Using Low Implantation Doses	USA	7378330
Controlled Cleaving Process	USA	7371660
Method for Fabricating Semiconductor Devices Using Strained Silicon Bearing Material	USA	7354815
Thin Handle Substrate Method and Structure for Fabricating Devices Using One or More Films Provided by a Layer Transfer Process	USA	7351644
Method and Device for Controlled Cleaving Process	USA	7348258
Surface Finishing of SOI Substrates Usina an EPI Process	USA	7253081
Thin Handle Substrate Method and Structure for Fabricating Devices Using One or More Films Provided by a Layer Transfer Process	USA	7166520
Controlled Cleaving Process	USA	7160790
Non-Contact Etch Annealing of Strained Layers	USA	7147709
Method and System for Fabricating Strained Layers for the Manufacture of Integrated Circuits	USA	7094666
Method and System for Source Switching and In-Situ Plasma Bonding	USA	7078317
Cleaving Process to Fabricate Multilayered Substrates Using Low Implantation Doses	USA	7056808
Treatment Method of Film Quality for the Manufacture of Substrates	USA	6969668
In Situ Plasma Wafer Bonding Method	USA	6908832
Gettering Technique for Wafers Made Using a Controlled Cleaving Process	USA	6890838
Smoothing Method for Cleaved Films Made Using a Release Layer	USA	6881644
Method and Device for Controlled Cleaving Process	USA	6790747
Method for Multi-Frequency Bonding	USA	6780759
In Situ Plasma Wafer Bonding Method	USA	6645828
Controlled Cleaving Process	USA	6632724
System for the Plasma Treatement of Large Area Substrates	USA	6632324
Controlled Cleavage Process Using Pressurized Fluid	USA	6582999
Silicon-On-Silicon Hybrid Wafer Assembly	USA	6558802
Substrate Cleaving Tool and Method	USA	6554046
Gettering Technique for Wafers Made Using a Controlled Cleaving Process	USA	6548382
Particle Distribution Method and Resulting Structure for a Layer Transfer Process	USA	6544862
Method for Fabricating Multi-Layered Substrates	USA	6534381
Controlled Cleavage Process and Device for Patterned Films	USA	6528391
Method for Non Mass Selected Ion Implant Profile Control	USA	6514838
Nozzle for Cleaving Substrates	USA	6513564
Controlled Cleavage Process Using Pressurized Fluid	USA	6511899
Cleaving Process to Fabricate Multilayered Substrates Using Low Implantation Doses	USA	6500732
Surfacing Finishing of SOI Substrates Using an EPI Process	USA	6489241
High Temperature Implant Method and Apparatus	USA	6458723
Controlled Cleavage Process and Resulting Device Using Beta Annealing	USA	6458672
Smoothing Method for Cleaved Films Made Using Thermal Treatment	USA	6455399
Method and System for Generating a Plurality of Donor Wafers and Handle Wafers Prior to an Order Being Placed by a Customer	USA	6448152
System for the Plasma Treatment of Large Area Substrates	USA	6338313
Controlled Cleavage Thin Film Separation Process Using a Reusable Substrate	USA	6335264
Cluster Tool System Software Using Plasma Immersion Ion Implantation	USA	6321134
Enhanced Plasma Mode, Method, and System for Plasma Immersion Ion Implantation	USA	6300227
Cleaved Silicon Thin Film With Rough Surface	USA	6294814
Pre-Semiconductor Process Implant and Post-Process Film Separation	USA	6291326
Controlled Cleavage Process and Device for Patterned Films Using a Release Layer	USA	6291314
Method and Device for Controlled Cleaving Process	USA	6291313
Controlled Cleavage Process Using Patterning	USA	6290804
Surface Finishing of SOI Substrates Using an EPI Process	USA	6287941
Method and Device for Controlled Cleaving Process	USA	6284631
Method for Non Mass Selected Ion Implant Profile Control	USA	6274459
Collection Devices for Plasma Immersion Ion Implantation	USA	6269765
Controlled Cleavage Process and Device for Patterned Films Using Patterned Implants	USA	6248649
Economical Silicon-on-Silicon Hybrid Wafer Assembly	USA	6245161
Contoured Platen Design for Plasma Immersion Ion Implantation	USA	6228176
Method for Surface Treatment of Substrates	USA	6221774
Substrate Cleaving Tool and Method	USA	6221740
Coated Platen Design for Plasma Immersion Ion Implantation	USA	6217724
Enhanced Plasma Mode and Computer System for Plasma Immersion Ion Implantation	USA	6213050
Cluster Tool Apparatus Using Plasma Immersion Ion Implantation	USA	6207005
Smoothing Method for Cleaved Films Made Using Thermal Treatment	USA	6204151
Device for Patterned Films	USA	6187110
Shielded Platen Design for Plasma Immersion Ion Implantation	USA	6186091
Pre-Semiconductor Process Implant and Post-Process Film Separation	USA	6184111
In Situ Plasma Wafer Bonding Method	USA	6180496
Treatment Method of Cleaved Film for the Manufacture of Substrates	USA	6171965

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Title - Description	Country	Patent No.
Controlled Cleavage Process and Resulting Device Using Beta Annealing	USA	6162705
Controlled Cleavage Thin Film Separation Process Using a Reusable Substrate	USA	6159825
Silicon-on-Silicon Wafer Bonding Process Using a Thin Film Blister-Separation Method	USA	6159824
Controlled Cleavage System Using Pressurized Fluid	USA	6155909
Cluster Tool Method Using Plasma Immersion Ion Implantation	USA	6153524
Pressurized Microbubble Thin Film Separation Process Using a Reusable Substrate	USA	6146979
Removable Liner Design for Plasma Immersion Ion Implantation	USA	6120660
Novel Distributed System and Code for Control and Automation of Plasma Immersion Ion Implanter	USA	6113735
Planarizing Technique for Multilayered Substrates	USA	6103599
Gettering Technique for Silicon-on-Insulator Wafers	USA	6083324
Perforated Shield for Plasma Immersion Ion Implantation	USA	6051073
Silicon-On-Silicon Hybrid Wafer Assembly	USA	6048411
Method for Controlled Cleaving Process	USA	6033974
Controlled Cleaving Process	USA	6013563
Reusable Substrate for Thin Film Separation	USA	6010579
Controlled Cleavage Process Using Pressurized Fluid	USA	5994207
Controlled Cleavage Process and Device for Patterned Films	USA	5985742
Tumbling Barrel Plasma Processor	USA	5945012
System for the Plasma Treatment of Large Area Substrates	USA	5653811
Layer Transfer of Films Utilizing Thermal Flux Regime For Energy Controlled Cleaving.	USA	8637382
Method and Device for Slicing a Shaped Silicon Ingot Using Layer Transfer	USA	8,623,137
Method and Structure for Fabricating Solar Cells Using a Thick Layer Transfer Process	USA	8,563,402
Race Track Configuration and Method for Wafering Silicon Solar Substrates	USA	8330126
Techniques for Forming Thin Films by Implantation with Reduced Channeling	USA	8329557
Layer Transfer of Films Utilizing Controlled Propagation	USA	8293619
Substrate Stiffness Method and Resulting Devices for Layer Transfer Process	USA	8241996
Apparatus and Method of Temperature Control During Cleaving Processes of Thick Film Materials	USA	8,222,119
Non-Contact Etch Annealing of Strained Layers	USA	8187377
Method and System for Continuous Large-Area Scanning Implantation Process	USA	8,153,513
Method for Fabricating Semiconductor Devices Using Strained Silicon Bearing Material	USA	8143165
Free-Standing Thickness of Single Crystal Material and Method Having Carrier Lifetimes	USA	8133800
Method and Structure for Thick Layer Transfer Using a Linear Accelerator	USA	8124499
Method and Structure for Fabricating Solar Cells Using a Thick Layer Transfer Process	USA	8110480
Method and Structure for Fabricating Multiple Tiled Regions onto a Plate Using a Controlled Cleaving Process	USA	8071463
Method and Structure for Fabricating Multiple Tiled Regions onto a Plate Using a Controlled Cleaving Process	USA	8012855
Controlled Process and Resulting Device	USA	8012852
Method and Structure for Fabricating Solar Cells Using A Layer Transfer Process	USA	8012851
Method and Structure for Fabricating Multiple Tiled Regions onto a Plate Using a Controlled Cleaving Process	USA	7911016
Method and Structure Using Selected Implant Angles Using a Linear Accelerator Process for Manufacture of Free Standing Films of Materials	USA	7910458
Liquid Based Substrate Method and Structure for Layer Transfer Applications	USA	7910456
Method and Structure for Fabricating Solar Cells Using A Layer Transfer Process	USA	7863157
Controlled Process and Resulting Device	USA	7846818
Method and Edge Region Structure Using Co-Implanted Particles for Layer Transfer Processes	USA	7811901
Method and Structure for Fabricating Solar Cells Using a Thick Layer Transfer Process	USA	7811900
Controlled Cleaving Process	USA	7781305
Controlled Process and Resulting Device	USA	7776717
Applications and Equipment of Substrate Stiffness Method and Resulting Devices for Layer Transfer Processes on Quartz or Glass	USA	7772088
Method and Structure for Fabricating Solar Cells Using a Layer Transfer Processes	USA	7759220
Controlled Process and Resulting Device	USA	7759217
Method and Structure for Fabricating Multiple Tiled Regions onto a Plate Using a Controlled Cleaving Process	USA	7674687
Method and Structure for Implanting Bonded Substrates for Electrical Conductivity	USA	7629666
Method and Device for Controlled Cleaving Process	USA	6486041
Generic Layer Transfer Methodology by Controlled Cleavage Process	USA	6391740
Controlled Cleavage Process Using Pressurized Fluid	USA	6013567
Method for Treating Semiconductor Material	Kingdom	2409340
Race Track Configuration and Method for Wafering Silicon Solar Substrates	Korea (South)	10-1163282
Free-Standing Thickness of Single Crystal Material and Method Having Carrier Lifetimes	Korea (South)	10-1154133
Method and Structure for Fabricating Bonded Substrate Structures Using Thermal Processing to Remove Oxygen Species	Korea (South)	10-0996539
An Apparatus and Method for Controlled Cleaving	Korea (South)	10-0810825
Plasma Treatment Apparatus for Large Area Substrates	Japan	4128217
Surface Finishing of SOI Substrates Using an EPI Process	Germany	1194949
Surface Finishing of SOI Substrates Using an EPI Process	France	1194949
Surface Finishing of SOI Substrates Using an EPI Process	EPO	1194949
System For The Plasma Treatment Of Large Area Substrates	EPO	0842307
A Controlled Cleavage Process	China	ZL98804976.7
Method for Fabricating Free Standing Thickness of Materials Using One or More Semiconductor Substrates	China	ZL200810009149.0
Method and Structure for Thick Layer Transfer Using A Linear Accelerator	China	ZL200780041135.0
Continuous Large-Area Scanning Implantation Process	China	ZL200780026734.5
Substrate Stiffness Method and Resulting Devices	China	ZL200680014752.7
A Method and Structure for Implanting Bonded Substrates for Electrical Conductivity	China	ZL2006101629001.1
An Apparatus and Method for Controlled Cleaving	China	ZL200580002085.6
Layer Transfer of Films Utilizing Controlled Shear Region	China	ZL 200910138229.0
Apparatus and Method of Temperature Control During Cleaving Processes of Thick Film Materials	China	ZL 200810006997.6
Method and Structure for Fabricating Solar Cells Using a Thick Layer Transfer Process	China	ZL 200780022933.9